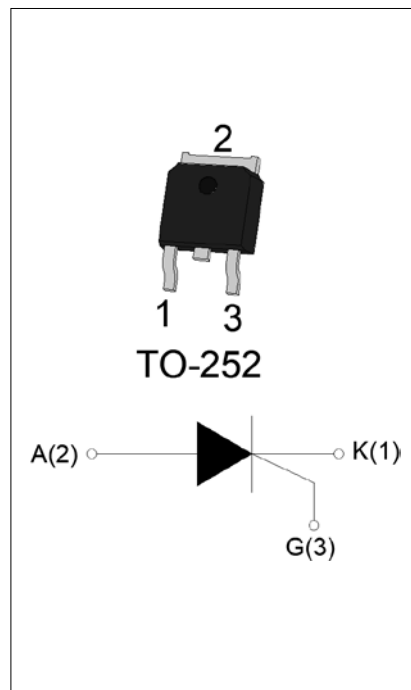




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151K-650R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference.

It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-252 is RoHS compliant.



MAIN FEATURES

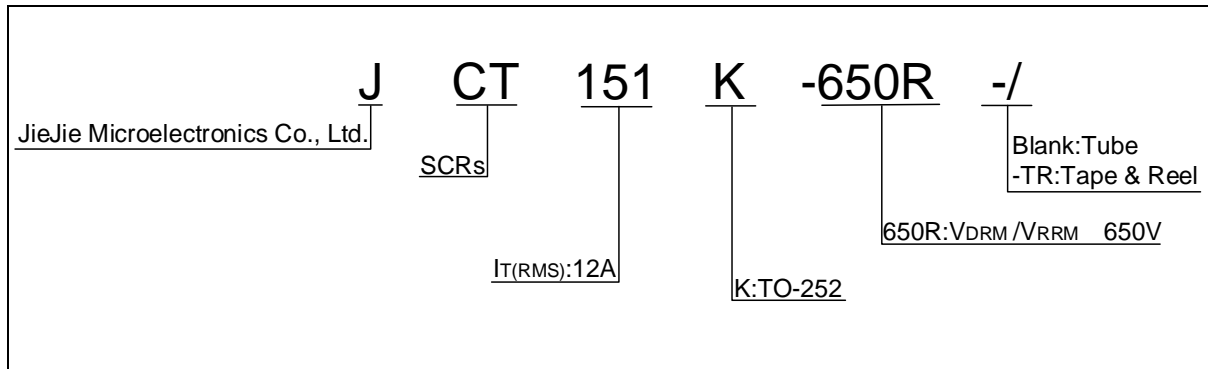
Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	650	V
I_{GT}	"15	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	650	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	650	V
Average on-state current ($T_c = 49^\circ C$)	$I_{T(AV)}$	7.5	A
RMS on-state current ($T_c = 49^\circ C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	120	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		132	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	100	A/s
Peak gate current ($t_p=20 \mu s, T_j=125^\circ C$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-stast1 re f 70.68 74)			

ORDERING INFORMATION



MARKING

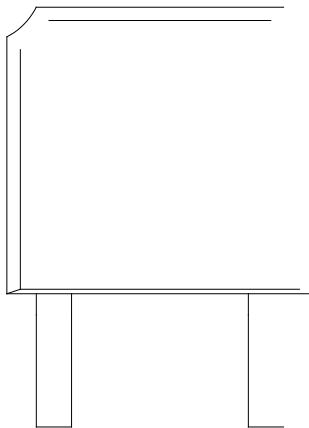


FIG.1: Maximum power dissipation versus RMS on-state current

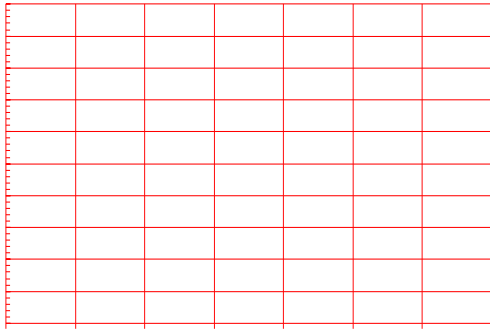


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

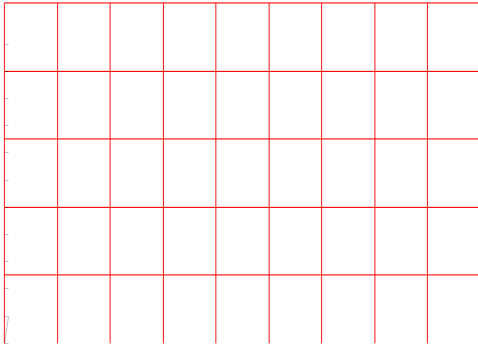
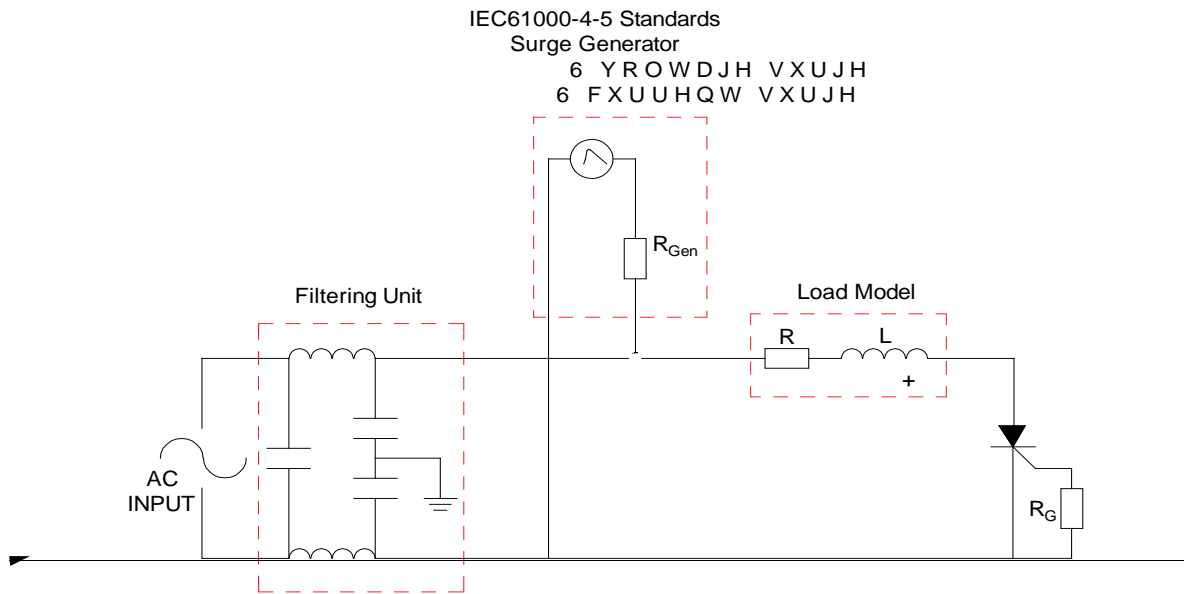


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



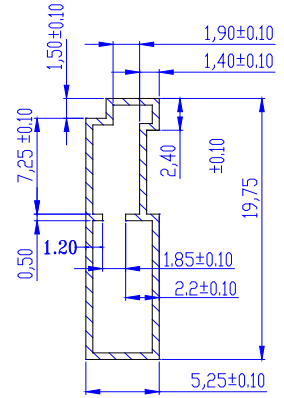
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(
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JCT151K-650R

JieJie M

DELIVERY MODE



Information furnished in this document is believed to be accurate and reliable.
However, Jiangsu JieJie Microelectronics Co., Ltd.